

Appl. No. 10/050,348

Amendments to the ClaimsRECEIVED
CENTRAL FAX CENTER
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Claims 1-40 (Canceled)

41. (Currently amended) A transistor structure, comprising:
a gate oxide layer on a semiconductive substrate, 5 Angstroms; 5X; the gate
oxide layer having a nitrogen-enriched region which is only in an upper half of the gate
oxide layer;

a conductive layer on the gate oxide layer; and
source/drain regions within the semiconductive substrate; the source/drain
regions being gatedly connected to one another by the conductive layer.

42. (Original) The structure of claim 41 wherein the conductive layer comprises
conductively-doped silicon.

43. (Original) The structure of claim 41 wherein the conductive layer comprises
p-type conductively-doped silicon.

Claims 44-52 (Canceled)